

**REMARKS**

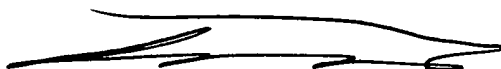
This preliminary amendment is directed to the above-referenced new application.

As filed, the application includes claims 1-16. Claims 9-10 and 16 have been amended to delete multiple dependency.

In view of the foregoing, it is respectfully submitted that the application is in condition for allowance and an early indication of the same is courteously solicited. The Examiner is respectfully requested to contact the undersigned by telephone at the below listed local telephone number, in order to expedite resolution of any remaining issues and further to expedite passage of the application to issue, if any further comments, questions or suggestions arise in connection with the application.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 12-0429 and please credit any excess fees to such deposit account.

Respectfully submitted,  
LALOS & KEEGAN



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**APPENDIX TO PATENT APPLICATION FILED CONCURRENTLY HEREWITH  
AMENDMENTS TO CLAIMS  
(DELETIONS IN BRACKETS AND ADDITIONS UNDERLINED)**

9. The crystalline silicon thin film semiconductor device according to claim 6 [or 8], wherein the fourth polycrystalline silicon layer has the same crystallographic orientation as the third polycrystalline silicon layer.

10. The crystalline silicon thin film semiconductor device according to claim 5[or 6], wherein the third and fourth polycrystalline silicon layers contain not less than 0.1% of hydrogen.

16. The process according to claim 14 [or 15], wherein the amorphous silicon layer has a thickness of not more than 50 nm.

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